

List of Publications in Papers in National/ International Journals:

1.	Current-voltage characteristics of Pd ₂ Si based Schottky diodes on p-type (111) silicon and evaluation of their barrier heights. Subhash Chand and Jitendra Kumar Solid State Electronics 38 , (1995) 1103-1104.
2.	Current-voltage characteristics and barrier parameters of Pd ₂ Si/p-Si(111) Schottky diodes in a wide temperature range. Subhash Chand and Jitendra Kumar Semiconductor Science & Technology 10 , (1995) 1680-1688.
3.	Current-transport in Pd ₂ Si/n-Si(100) Schottky barrier diodes at low temperatures. Subhash Chand and Jitendra Kumar Applied Physics A 63 , (1996) 171-178.
4.	On the Existence of a barrier heights distribution in Pd ₂ Si/Si Schottky diodes. Subhash Chand and Jitendra Kumar Journal of Applied Physics 80 , (1996) 288-294
5.	Evidence for the double distribution of barrier heights in Pd ₂ Si/n-Si Schottky diodes from I-V-T measurements. Subhash Chand and Jitendra Kumar Semiconductor Science & Technology 11 , (1996) 1203-1208
6.	Electron transport and barrier inhomogeneities in palladium silicide Schottky diodes. Subhash Chand and Jitendra Kumar Applied Physics A 65 , (1997) 497-503
7.	Simulation and analysis of current-voltage characteristics of Schottky diodes containing barrier inhomogeneities. Subhash Chand and Jitendra Kumar Semiconductor Science & Technology 12 , (1997) 899-906
8.	Effects of barrier height distribution on the behavior of a Schottky diode. Subhash Chand and Jitendra Kumar Journal of Applied Physics 82 , (1997) 5005-10
9.	Origin of non-linear current-voltage characteristics of metal-semiconductor contacts: A numerical study Subhash Chand Indian Journal of Engineering and Materials Sciences 7 , (2000) 268-273
10.	An accurate approach for analyzing inhomogeneous Schottky diodes with a Gaussian distribution of barrier heights. Subhash Chand Semiconductor Science & Technology 17 , (2002) L36-L40
11.	On intersecting behaviour of current-voltage characteristics of inhomogeneous Schottky diodes at low temperatures. Subhash Chand Semiconductor Science & Technology 19 , (2004) 82-86

12.	Analysis of current-voltage characteristics of inhomogeneous Schottky diodes at low temperatures. Subhash Chand and Saroj Bala Applied Surface Science 252 (2005) 358-363
13.	A comparative study of numerical and analytical approaches of simulating inhomogeneous Schottky diodes characteristics Subhash Chand and Saroj Bala Semiconductor Science & Technology 20 , (2005) 1143-1148
14.	Theoretical evidence for random variation of series resistance of elementary diodes in inhomogeneous Schottky contacts Subhash Chand Physica B 373 (2006) 284-290.
15.	Simulation studies of current transport in metal-insulator-semiconductor Schottky barrier diodes Subhash Chand and Saroj Bala Physica B 390 , (2007) 179-184.
16.	Synthesis and Electrical Characterization of Self-Supported Conducting Polypyrrole-Poly(vinylidene fluoride) Composite Films <i>Manish Taunk, Atul Kapil and Subhash Chand</i> The Open Macromolecules Journal, 2 (2008) 74-79.
17.	Preparation and characterization of chemically synthesized poly(N-methylaniline) <i>Atul Kapil, Manish Taunk and Subhash Chand</i> Synthetic Metals 159 , (2009) 1267.
18.	Low Temperature Charge Transport Study in p-Toluenesulfonic Acid Doped Polyaniline <i>Atul Kapil, Manish Taunk and Subhash Chand</i> Asian Journal of Chemistry Vol. 21 , No. 10 (2009), S138-142
19.	Preparation and charge transport studies of chemically synthesized polyaniline <i>Atul Kapil, Manish Taunk and Subhash Chand</i> J Mater Sci: Mater. Electron. 21 , 399-404 (2010).
20.	Hopping and tunneling transport over a wide temperature range in chemically synthesized doped and undoped polypyrrole <i>Manish Taunk, Atul Kapil, Subhash Chand</i> Solid State Communication 150 (2010) 1766-1769
21.	Chemical synthesis and low temperature electrical transport in polypyrrole doped with sodium bis(2-ethylhexyl) sulfosuccinate. Manish Taunk, Atul Kapil and Subhash Chand J Mater Sci: Mater. Electron. 22 (2011)p136–142
22.	Study of synthesis and temperature dependence of dc conductivity in the low temperature range for Poly(N-methylaniline) <i>Atul Kapil, Manish Taunk and Subhash Chand</i> Journal of Electronic Materials (In Press)
23.	Current voltage characteristics of Schottky diode simulated using semiconductor device equations Priyanka Kaushal, Subhash Chand , and Jozef Osvald International Journal of Electronics, in press.

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24.	<p>Effect of inverse doped surface layer in Schottky barrier modification: A numerical study</p> <p>Subhash Chand, Priyanka Kaushal and Jozef Osvald</p> <p>Journal of Electronic Materials, in press.</p> <p>DOI: 10.1007/s11664-012-2234-z</p>
25.	<p>Numerical simulation study of Schottky diode characteristics with inverse doped surface layer</p> <p>Subhash Chand, Priyanka Kaushal and Jozef Osvald</p> <p>Materials Science in Semiconductor Processing, in press.</p> <p>DOI: http://dx.doi.org/10.1016/j.mssp.2012.08.002</p>